

PHB45NQ10T

N-channel TrenchMOS standard level FET Rev. 02 — 8 July 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC convertors

Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I_D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V$	-	-	47	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	-	150	W
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	22	25	mΩ
Dynamic cl	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 45 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C}$	-	25	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHB45NQ10T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}$	-	33	Α
		V _{GS} = 10 V; T _{mb} = 25 °C	-	47	Α
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	188	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
Is	source current	T _{mb} = 25 °C	-	47	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	188	Α
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 40 A; V_{sup} ≤ 25 V; unclamped; t_p = 100 µs; R_{GS} = 50 Ω	-	260	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; \text{ unclamped}$	-	47	Α

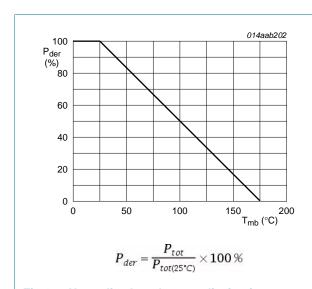


Fig 1. Normalized total power dissipation as a function of mounting base temperature

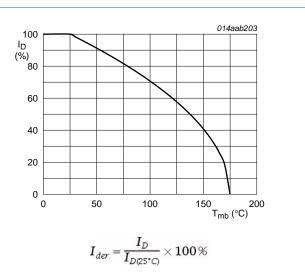
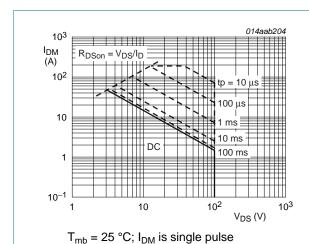


Fig 2. Normalized continuous drain current as a function of mounting base temperature

PHB45NQ10T

N-channel TrenchMOS standard level FET



ig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

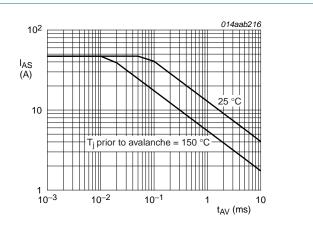


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W

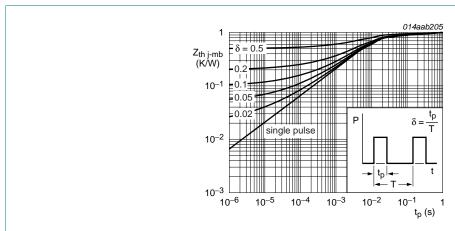


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
33(11)	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I _{DSS} drain leakage cur	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS} gate leakage curre	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nΑ
R _{DSon} drain-source on-state		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C}$	-	-	68	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	22	25	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	61	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	13	-	nC
Q_{GD}	gate-drain charge		-	25	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2600	-	рF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$	-	340	-	pF
C _{rss}	reverse transfer capacitance		-	195	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}$	-	72	-	ns
t _{d(off)}	turn-off delay time		-	69	-	ns
t _f	fall time		-	58	-	ns
L _D	internal drain inductance	from tab to centre of die ; $T_j = 25$ °C	-	3.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-drai	n diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.87	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	82	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	0.26	-	μC

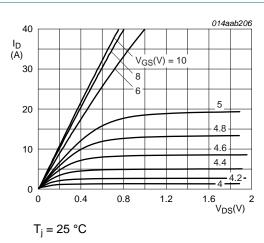
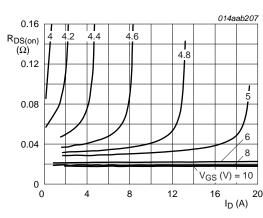


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values

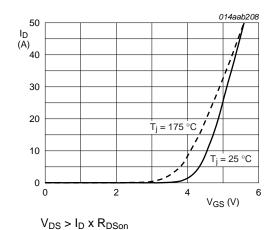
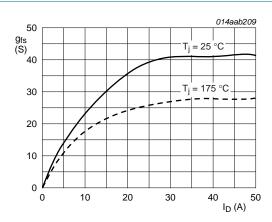


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

Fig 9. Forward transconductance as a function of drain current; typical values

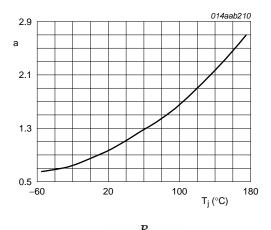
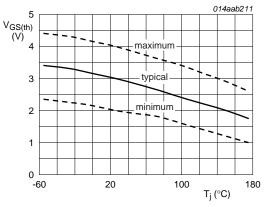


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature

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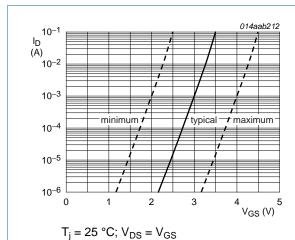
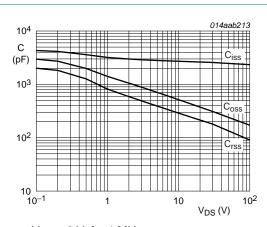


Fig 12. Sub-threshold drain current as a function of gate-source voltage



 $V_{GS} = 0 V$; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

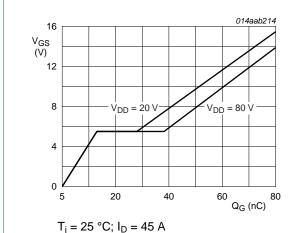
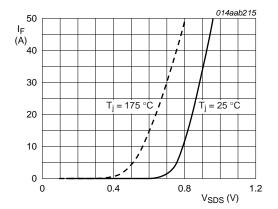


Fig 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

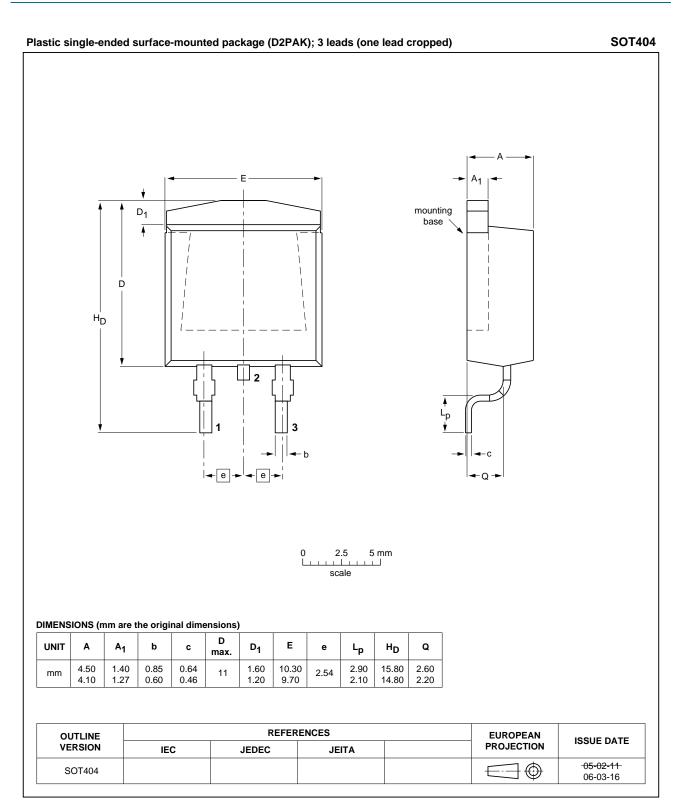


Fig 16. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHB45NQ10T v.2	20100708	Product data sheet	-	PHB_PHP_PHW45NQ10T v.1
Modifications:		this data sheet has been NXP Semiconductors.	en redesigned to o	comply with the new identity
	 Legal texts ha 	ave been adapted to the	new company na	ame where appropriate.
	 Type number 	PHB45NQ10T separate	ed from data shee	t PHB_PHP_PHW45NQ10T v.1.
PHB_PHP_PHW45NQ10T v.1	19990801	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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10 of 12

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N-channel TrenchMOS standard level FET

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values3
5	Thermal characteristics4
6	Characteristics5
7	Package outline
8	Revision history
9	Legal information10
9.1	Data sheet status
9.2	Definitions10
9.3	Disclaimers
9.4	Trademarks11
10	Contact information

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